# 80SQ045N

**Preferred Device** 

# **Axial Lead Rectifier**

These devices employ the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

### **Features**

- High Current Capability
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency
- Highly Stable Oxide Passivated Junction
- Guard-Ring for Stress Protection
- Low Forward Voltage
- High Surge Capacity
- These are Pb-Free Devices\*

### **Mechanical Characteristics:**

- Case: Epoxy, Molded
- Weight: 1.1 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 220°C Max. for 10 Seconds, 1/16" from Case
- Polarity: Cathode indicated by Polarity Band
- ESD Protection: Human Body Model > 4000 V (Class 3) Machine Model > 400 V (Class C)

### **MAXIMUM RATINGS**

Rating	Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	45	V
Average Rectified Forward Current $T_L = 75^{\circ}C$ (Psi <sub>JL</sub> = 12°C/W, P.C. Board Mounting, Note 2)	IO	8.0	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	140	Α
Operating and Storage Junction Temperature Range (Reverse Voltage Applied)	T <sub>J</sub> , T <sub>stg</sub>	-65 to +125	°C
Voltage Rate of Change (Rated V <sub>R</sub> )	dv/dt	10	V/ns

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



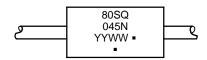
# ON Semiconductor®

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# SCHOTTKY BARRIER RECTIFIER 8.0 AMPERES



## **MARKING DIAGRAM**



YY = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
80SQ045N	Axial Lead*	500 Units/Box
80SQ045NG	Axial Lead*	500 Units/Box
80SQ045NRL	Axial Lead*	1500/Tape & Reel
80SQ045NRLG	Axial Lead*	1500/Tape & Reel

- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- \*This package is inherently Pb-Free.

**Preferred** devices are recommended choices for future use and best overall value.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

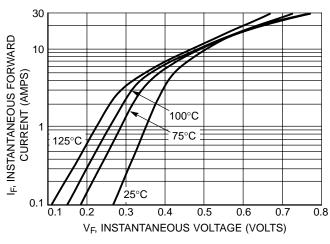
### THERMAL CHARACTERISTICS

Characteristic	Symbol	0.9 in x 0.9 in Copper Pad Size	6.75 in x 6.75 in Copper Pad Size	Unit
Thermal Resistance, Junction–to–Lead (See Note 2 – Mounting Data)	$R_{ heta JL}$	13	12	°C/W
Thermal Resistance, Junction–to–Ambient (See Note 2 – Mounting Data)	$R_{\theta JA}$	50	40	

# **ELECTRICAL CHARACTERISTICS** (T<sub>L</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) $(i_F = 8.0 \text{ A}, T_L = 25^{\circ}\text{C})$	V <sub>F</sub>	0.55	V
Maximum Instantaneous Reverse Current @ Rated dc Voltage (Note 1) $T_L = 25^{\circ}C$ $T_L = 100^{\circ}C$	i <sub>R</sub>	1.0 50	mA

<sup>1.</sup> Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.



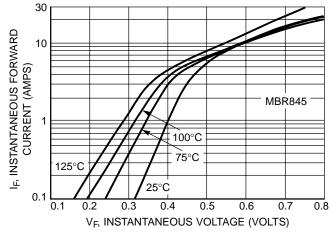
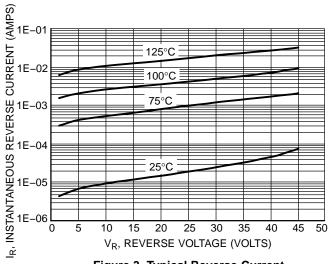


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage





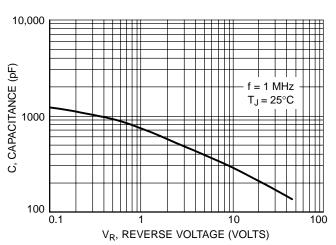


Figure 4. Typical Capacitance

## 80SQ045N

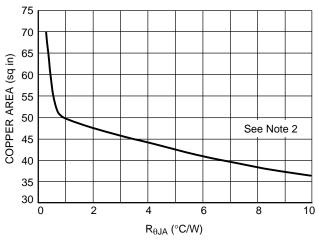


Figure 5. R<sub>θJA</sub> versus Copper Area

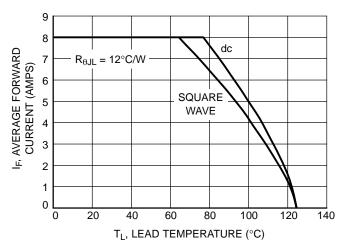


Figure 6. Current Derating - Lead

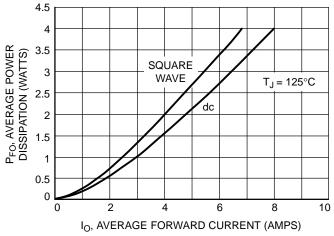
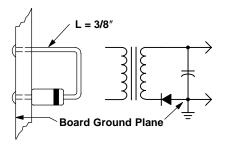


Figure 7. Forward Power Dissipation

# **NOTE 2 — MOUNTING DATA**

## **Mounting Method**

P.C. Board with 6.75 sq. in. copper surface.



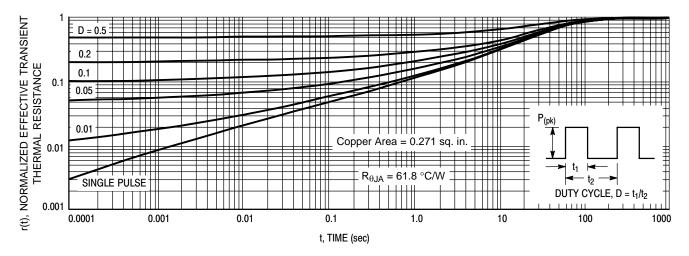
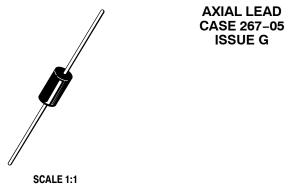
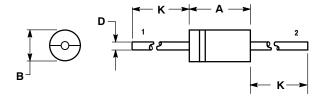


Figure 8. Thermal Response, Junction-to-Ambient



**DATE 06/06/2000** 



- NOTES:

  1. DIMENSIONS AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. 267-04 OBSOLETE, NEW STANDARD 267-05.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.287	0.374	7.30	9.50
В	0.189	0.209	4.80	5.30
D	0.047	0.051	1.20	1.30
K	1.000		25 40	

STYLE 2: NO POLARITY STYLE 1: PIN 1. CATHODE (POLARITY BAND) 2. ANODE

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